

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

priority Application Serial No. .... 09/633,556  
priority Filing Date ..... August 7, 2000  
Inventor ..... Gurtej S. Sandhu et al.  
Assignee ..... Micron Technology, Inc.  
priority Group Art Unit ..... 2813  
priority Examiner ..... Laura M. Schillinger  
Attorney's Docket No. .... MI22-1897  
Title: Methods of Forming Transistors (As Amended)

**PRELIMINARY AMENDMENT**

To:Box Patent Application  
Assistant Commissioner for Patents  
Washington, D.C. 20231

From: David G. Latwesen, Ph.D. (Tel. 509-624-4276; Fax 509-838-3424)  
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**In the Specification**

Replace the title with --Methods of Forming Transistors--.

At page 1, before the "Technical Field" section, please insert:

**--CROSS REFERENCE TO RELATED APPLICATION**

This patent resulted from a divisional application of U.S. Patent  
Application Serial No. 09/633,556, which was filed on August 7, 2000.--.

## In the Claims

Claims 1-19 and 41-47 are canceled.

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**REMARKS**

Claims 1-19 and 41-47 are canceled, leaving claims 20-40 pending in the application. Applicant requests substantive examination of pending claims 20-40.

Respectfully submitted,

Dated: 11/15/02

By: 

David G. Latwesen, Ph.D.  
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**VERSION WITH MARKINGS TO SHOW CHANGES MADE  
ACCOMPANYING PRELIMINARY AMENDMENT**

**In the Specification**

The replacement specification paragraphs incorporate the following amendments. Underlines indicate insertions and ~~strikeouts~~ indicate deletions.

The title is amended as follows: ~~Transistor Structures, Methods of  
Incorporating Nitrogen into Silicon-Oxide-Containing Layers; and Methods of  
Forming Transistors~~

The following is inserted on p. 1 before the "Technical Field" section,

**CROSS REFERENCE TO RELATED APPLICATION**

This patent resulted from a divisional application of U.S. Patent Application  
Serial No. 09/633,556, which was filed on August 7, 2000.

**In the Claims**

Claims 1-19 and 41-47 are canceled.

**-END OF DOCUMENT-**

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